

December 1992

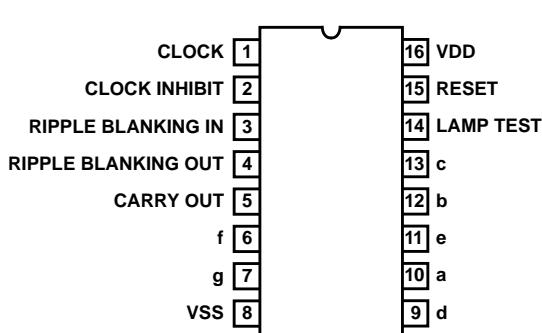
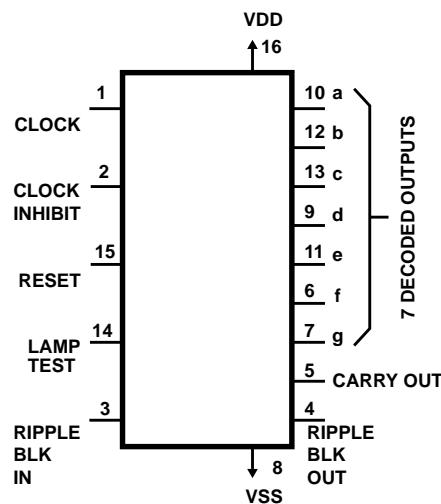
CMOS Decade Counter/Divider

Features

- High Voltage Types (20V Rating)
- Decoded 7 Segment Display Outputs and Ripple Blanking
- Counter and 7 Segment Decoding in One Package
- Easily Interfaced with 7 Segment Display Types
- Fully Static Counter Operation DC to 6MHz (typ.) at VDD = 10V
- Ideal for Low-Power Displays
- “Ripple Blanking” and Lamp Test
- 100% Tested for Quiescent Current at 20V
- Standardized Symmetrical Output Characteristics
- 5V, 10V and 15V Parametric Ratings
- Schmitt-Triggered Clock Inputs
- Meets All Requirements of JEDEC Tentative Standards No. 13B, “Standard Specifications for Description of “B” Series CMOS Device’s

Applications

- Decade Counting 7 Segment Decimal Display
- Frequency Division 7 Segment Decimal Displays
- Clocks, Watches, Timers (e.g. ÷ 60, ÷ 60, ÷12 Counter/Display)
- Counter/Display Driver For Meter Applications

PinoutCD4033BMS
TOP VIEW**Functional Diagram**

The CD4033BMS has provisions for automatic blanking of the non-significant zeros in a multi-digit decimal number which results in an easily readable display consistent with normal writing practice. For example, the number 0050.0700 in an eight digit display would be displayed as 50.07. Zero suppression on the integer side is obtained by connecting the RBI terminal of the CD4033BMS associated with the most significant digit in the display to a low-level voltage and connecting the RBO terminal of that stage to the RBI terminal of the CD4033BMS in the next-lower significant position in the display. This procedure is continued for each succeeding CD4033BMS on the integer side of the display.

On the fraction side of the display the RBI of the CD4033BMS associated with the least significant bit is connected to a low-level voltage and the RBO of that CD4033BMS is connected to the RBI terminal of the CD4033BMS in the next more-significant-bit position. Again, this procedure is continued for all CD4033BMS's on the fraction side of the display.

In a purely fractional number the zero immediately preceding the decimal point can be displayed by connecting the RBI of that stage to a high level voltage (instead of to the RBO of the next more-significant-stage). For example: optional zero → 0.7346. Likewise, the zero in a number such as 763.0 can be displayed by connecting the RBI of the CD4033BMS associated with it to a high-level voltage.

Ripple blanking of non-significant zeros provides an appreciable savings in display power.

The CD4033BMS has a LAMP TEST input which, when connected to a high-level voltage, overrides normal decoder operation and enables a check to be made on possible display malfunctions by putting the seven outputs in the high state.

The CD4033BMS are supplied in these 16 lead outline packages:

Braze Seal DIP H4W

Frit Seal DIP H2R

Ceramic Flatpack H6W

Logic Diagram

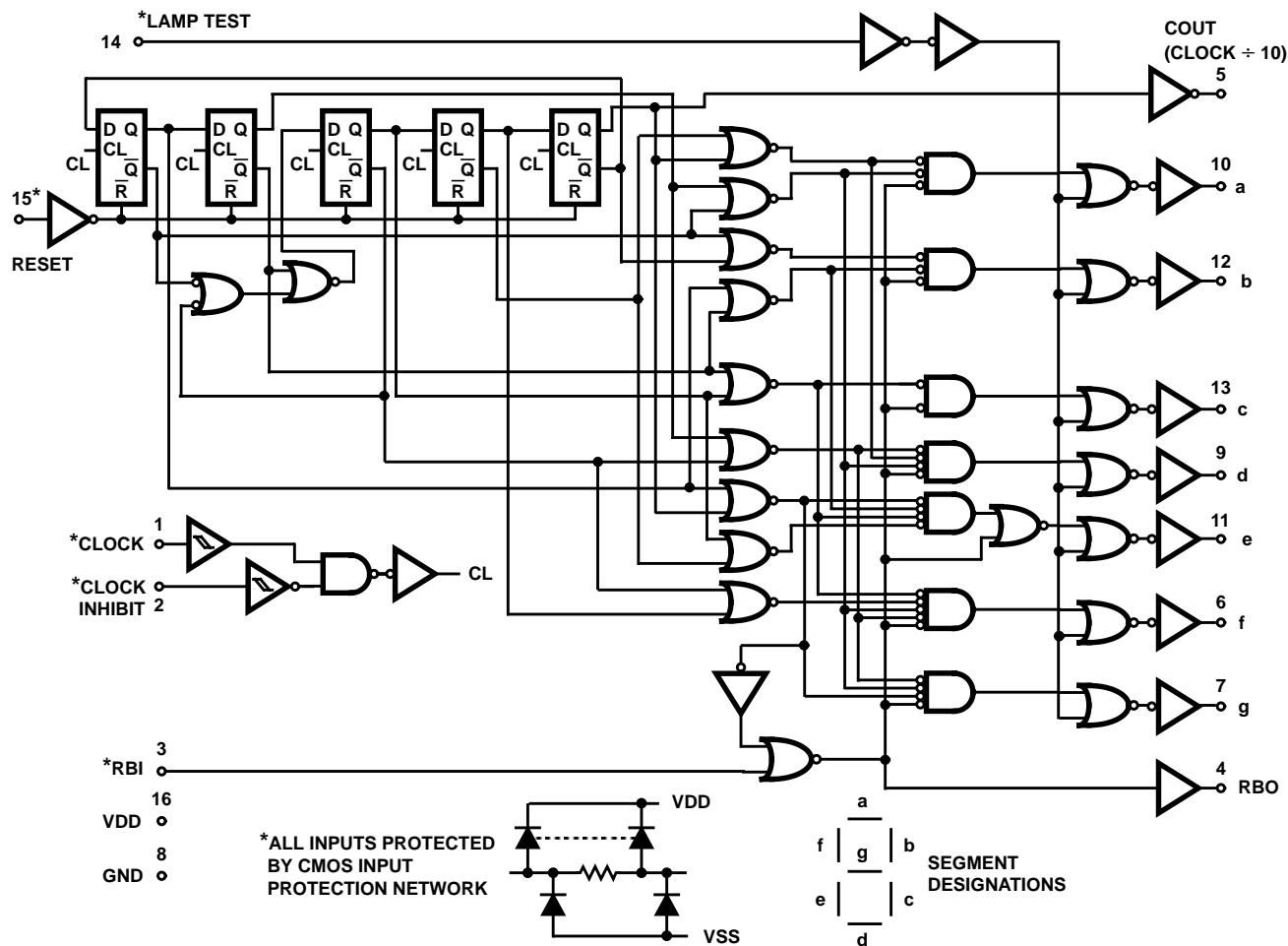


FIGURE 1. CD4033BMS

Specifications CD4033BMS

Absolute Maximum Ratings

DC Supply Voltage Range, (VDD)	-0.5V to +20V (Voltage Referenced to VSS Terminals)
Input Voltage Range, All Inputs	-0.5V to VDD +0.5V
DC Input Current, Any One Input	±10mA
Operating Temperature Range.....	-55°C to +125°C Package Types D, F, K, H
Storage Temperature Range (TSTG).....	-65°C to +150°C
Lead Temperature (During Soldering)	+265°C At Distance 1/16 ± 1/32 Inch (1.59mm ± 0.79mm) from case for 10s Maximum

Reliability Information

Thermal Resistance	θ_{ja}	θ_{jc}
Ceramic DIP and FRIT Package	80°C/W	20°C/W
Flatpack Package	70°C/W	20°C/W
Maximum Package Power Dissipation (PD) at +125°C		
For TA = -55°C to +100°C (Package Type D, F, K)	500mW	
For TA = +100°C to +125°C (Package Type D, F, K)	Derate Linearity at 12mW/°C to 200mW	
Device Dissipation per Output Transistor	100mW	
For TA = Full Package Temperature Range (All Package Types)		
Junction Temperature		+175°C

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS (NOTE 1)	GROUP A SUBGROUPS	TEMPERATURE	LIMITS		UNITS	
					MIN	MAX		
Supply Current	IDD	VDD = 20V, VIN = VDD or GND	1	+25°C	-	10	µA	
			2	+125°C	-	1000	µA	
		VDD = 18V, VIN = VDD or GND	3	-55°C	-	10	µA	
Input Leakage Current	IIL	VIN = VDD or GND	VDD = 20	1	+25°C	-100	-	nA
				2	+125°C	-1000	-	nA
			VDD = 18V	3	-55°C	-100	-	nA
Input Leakage Current	IIH	VIN = VDD or GND	VDD = 20	1	+25°C	-	100	nA
				2	+125°C	-	1000	nA
			VDD = 18V	3	-55°C	-	100	nA
Output Voltage	VOL15	VDD = 15V, No Load	1, 2, 3	+25°C, +125°C, -55°C	-	50	mV	
Output Voltage	VOH15	VDD = 15V, No Load (Note 3)	1, 2, 3	+25°C, +125°C, -55°C	14.95	-	V	
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.4V	1	+25°C	0.53	-	mA	
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0.5V	1	+25°C	1.4	-	mA	
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1.5V	1	+25°C	3.5	-	mA	
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V	1	+25°C	-	-0.53	mA	
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.5V	1	+25°C	-	-1.8	mA	
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9.5V	1	+25°C	-	-1.4	mA	
Output Current (Source)	IOH15	VDD = 15V, VOUT = 13.5V	1	+25°C	-	-3.5	mA	
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10µA	1	+25°C	-2.8	-0.7	V	
P Threshold Voltage	VPTH	VSS = 0V, IDD = 10µA	1	+25°C	0.7	2.8	V	
Functional	F	VDD = 2.8V, VIN = VDD or GND	7	+25°C	VOH > VDD/2	VOL < VDD/2	V	
		VDD = 20V, VIN = VDD or GND	7	+25°C				
		VDD = 18V, VIN = VDD or GND	8A	+125°C				
		VDD = 3V, VIN = VDD or GND	8B	-55°C				
Input Voltage Low (Note 2)	VIL	VDD = 5V, VOH > 4.5V, VOL < 0.5V	1, 2, 3	+25°C, +125°C, -55°C	-	1.5	V	
Input Voltage High (Note 2)	VIH	VDD = 5V, VOH > 4.5V, VOL < 0.5V	1, 2, 3	+25°C, +125°C, -55°C	3.5	-	V	
Input Voltage Low (Note 2)	VIL	VDD = 15V, VOH > 13.5V, VOL < 1.5V	1, 2, 3	+25°C, +125°C, -55°C	-	4	V	
Input Voltage High (Note 2)	VIH	VDD = 15V, VOH > 13.5V, VOL < 1.5V	1, 2, 3	+25°C, +125°C, -55°C	11	-	V	

- NOTES: 1. All voltages referenced to device GND, 100% testing being implemented.
 2. Go/No Go test with limits applied to inputs.
 3. For accuracy, voltage is measured differentially to VDD. Limit is 0.050V max.

Specifications CD4033BMS

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS (NOTE 1, 2)	GROUP A SUBGROUPS	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Propagation Delay Clock To Carry Out	TPHL1 TPLH1	VDD = 5V, VIN = VDD or GND	9	+25°C	-	500	ns
			10, 11	+125°C, -55°C	-	675	ns
Propagation Delay Clock To Decode Out	TPHL2 TPLH2	VDD = 5V, VIN = VDD or GND	9	+25°C	-	700	ns
			10, 11	+125°C, -55°C	-	945	ns
Propagation Delay Reset To Carry Out	TPLH3	VDD = 5V, VIN = VDD or GND	9	+25°C	-	550	ns
			10, 11	+125°C, -55°C	-	743	ns
Propagation Delay Reset To Decode Out	TPHL4 TPLH4	VDD = 5V, VIN = VDD or GND	9	+25°C	-	600	ns
			10, 11	+125°C, -55°C	-	810	ns
Transition Time	TTHL TTLH	VDD = 5V, VIN = VDD or GND	9	+25°C	-	200	ns
			10, 11	+125°C, -55°C	-	270	ns
Maximum Clock Input Frequency	FCL	VDD = 5V, VIN = VDD or GND	9	+25°C	2.5	-	MHz
			10, 11	+125°C, -55°C	1.85	-	MHz

NOTES:

1. VDD = 5V, CL = 50pF, RL = 200K
2. -55°C and +125°C limits guaranteed, 100% testing being implemented.

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Supply Current	IDD	VDD = 5V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	5	µA
				+125°C	-	150	µA
		VDD = 10V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	10	µA
				+125°C	-	300	µA
		VDD = 15V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	10	µA
				+125°C	-	600	µA
Output Voltage	VOL	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOL	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOH	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	4.95	-	V
Output Voltage	VOH	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	9.95	-	V
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.4V	1, 2	+125°C	0.36	-	mA
				-55°C	0.64	-	mA
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0.5V	1, 2	+125°C	0.9	-	mA
				-55°C	1.6	-	mA
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1.5V	1, 2	+125°C	2.4	-	mA
				-55°C	4.2	-	mA
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V	1, 2	+125°C	-	-0.36	mA
				-55°C	-	-0.64	mA
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.5V	1, 2	+125°C	-	-1.15	mA
				-55°C	-	-2.0	mA
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9.5V	1, 2	+125°C	-	-0.9	mA
				-55°C	-	-2.6	mA

Specifications CD4033BMS

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Output Current (Source)	IOH15	VDD = 15V, VOUT = 13.5V	1, 2	+125°C	-	-2.4	mA
				-55°C	-	-4.2	mA
Input Voltage Low	VIL	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	-	3	V
Input Voltage High	VIH	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	+7	-	V
Propagation Delay Clock To Carry Out	TPHL1 TPLH1	VDD = 10V	1, 2, 3	+25°C	-	200	ns
		VDD = 15V	1, 2, 3	+25°C	-	150	ns
Propagation Delay Clock To Decode Out	TPHL2 TPLH2	VDD = 10V	1, 2, 3	+25°C	-	250	ns
		VDD = 15V	1, 2, 3	+25°C	-	180	ns
Propagation Delay Reset To Carry Out	TPLH3	VDD = 10V	1, 2, 3	+25°C	-	240	ns
		VDD = 15V	1, 2, 3	+25°C	-	160	ns
Propagation Delay Reset To Decode Out	TPHL4 TPLH4	VDD = 10V	1, 2, 3	+25°C	-	250	ns
		VDD = 15V	1, 2, 3	+25°C	-	180	ns
Transition Time	TTHL TTLH	VDD = 10V	1, 2, 3	+25°C	-	100	ns
		VDD = 15V	1, 2, 3	+25°C	-	50	ns
Maximum Clock Input Frequency	FCL	VDD = 10V	1, 2, 3	+25°C	5.5	-	MHz
		VDD = 15V	1, 2, 3	+25°C	8	-	MHz
Minimum Reset Pulse Width	TW	VDD = 5V	1, 2, 3	+25°C	-	120	ns
		VDD = 10V	1, 2, 3	+25°C	-	100	ns
		VDD = 15V	1, 2, 3	+25°C	-	50	ns
Minimum Reset Removal Time	TREM	VDD = 5V	1, 2, 3	+25°C	-	30	ns
		VDD = 10V	1, 2, 3	+25°C	-	15	ns
		VDD = 15V	1, 2, 3	+25°C	-	10	ns
Minimum Clock Pulse Width	TW	VDD = 5V	1, 2, 3	+25°C	-	220	ns
		VDD = 10V	1, 2, 3	+25°C	-	100	ns
		VDD = 15V	1, 2, 3	+25°C	-	80	ns
Input Capacitance	CIN	Any Input	1, 2	+25°C	-	7	pF

NOTES:

1. All voltages referenced to device GND.
2. The parameters listed on Table 3 are controlled via design or process and are not directly tested. These parameters are characterized on initial design release and upon design changes which would affect these characteristics.
3. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

TABLE 4. POST IRRADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Supply Current	IDD	VDD = 20V, VIN = VDD or GND	1, 4	+25°C	-	25	µA
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10µA	1, 4	+25°C	-2.8	-0.2	V
N Threshold Voltage Delta	ΔVTN	VDD = 10V, ISS = -10µA	1, 4	+25°C	-	±1	V
P Threshold Voltage	VTP	VSS = 0V, IDD = 10µA	1, 4	+25°C	0.2	2.8	V
P Threshold Voltage Delta	ΔVTP	VSS = 0V, IDD = 10µA	1, 4	+25°C	-	±1	V
Functional	F	VDD = 18V, VIN = VDD or GND	1	+25°C	VOH > VDD/2	VOL < VDD/2	V
		VDD = 3V, VIN = VDD or GND					

Specifications CD4033BMS

TABLE 4. POST IRRADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Propagation Delay Time	TPHL TPLH	VDD = 5V	1, 2, 3, 4	+25°C	-	1.35 x +25°C Limit	ns

NOTES: 1. All voltages referenced to device GND.

3. See Table 2 for +25°C limit.

2. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

4. Read and Record

TABLE 5. BURN-IN AND LIFE TEST DELTA PARAMETERS +25°C

PARAMETER	SYMBOL	DELTA LIMIT
Supply Current - MSI-2	IDD	± 1.0µA
Output Current (Sink)	IOL5	± 20% x Pre-Test Reading
Output Current (Source)	IOH5A	± 20% x Pre-Test Reading

TABLE 6. APPLICABLE SUBGROUPS

CONFORMANCE GROUP	MIL-STD-883 METHOD	GROUP A SUBGROUPS	READ AND RECORD
Initial Test (Pre Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test 1 (Post Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test 2 (Post Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note 1)	100% 5004	1, 7, 9, Deltas	
Interim Test 3 (Post Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note 1)	100% 5004	1, 7, 9, Deltas	
Final Test	100% 5004	2, 3, 8A, 8B, 10, 11	
Group A	Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11	
Group B	Subgroup B-5	Sample 5005	Subgroups 1, 2, 3, 9, 10, 11
	Subgroup B-6	Sample 5005	1, 7, 9
Group D	Sample 5005	1, 2, 3, 8A, 8B, 9	Subgroups 1, 2 3

NOTE: 1. 5% Parameteric, 3% Functional; Cumulative for Static 1 and 2.

TABLE 7. TOTAL DOSE IRRADIATION

CONFORMANCE GROUPS	MIL-STD-883 METHOD	TEST		READ AND RECORD	
		PRE-IRRAD	POST-IRRAD	PRE-IRRAD	POST-IRRAD
Group E Subgroup 2	5005	1, 7, 9	Table 4	1, 9(Table 4

TABLE 8. BURN-IN AND IRRADIATION TEST CONNECTIONS

FUNCTION	OPEN	GROUND	VDD	9V ± 0.5V	OSCILLATOR	
					50kHz	25kHz
PART NUMBER						
Static Burn-In 1 (Note 1)	4 - 7, 9 - 14	1 - 3, 8, 15	16			
Static Burn-In 2 (Note 1)	1, 2, 14, 15	3 - 6, 8, 10 - 13	7, 9, 16			
Dynamic Burn-In (Note 1)	-	2, 8, 15	3, 16	4 - 7, 9 - 13	1	
Irradiation (Note 2)	4 - 7, 9 - 14	8	1 - 3, 15, 16			
PART NUMBER CD4033BMS						

Specifications CD4033BMS

TABLE 8. BURN-IN AND IRRADIATION TEST CONNECTIONS

FUNCTION	OPEN	GROUND	VDD	9V ± 0.5V	OSCILLATOR	
					50kHz	25kHz
Static Burn-In 1 Note 1	4 - 7, 9 - 13	1 - 3, 8, 14, 15	16			
Static Burn-In 2 Note 1	4 - 7, 9 - 13	8	1 - 3, 14 - 16			
Dynamic Burn-In Note 1	-	2, 3, 8, 14, 15	16	4 - 7, 9 - 13	1	
Irradiation Note 2	4 - 7, 9 - 13	8	1 - 3, 14 - 16			

NOTE:

1. Each pin except VDD and GND will have a series resistor of $10K \pm 5\%$, $VDD = 18V \pm 0.5V$
2. Each pin except VDD and GND will have a series resistor of $47K \pm 5\%$; Group E, Subgroup 2, sample size is 4 dice/wafer, 0 failures, $VDD = 10V \pm 0.5V$

Timing Diagram

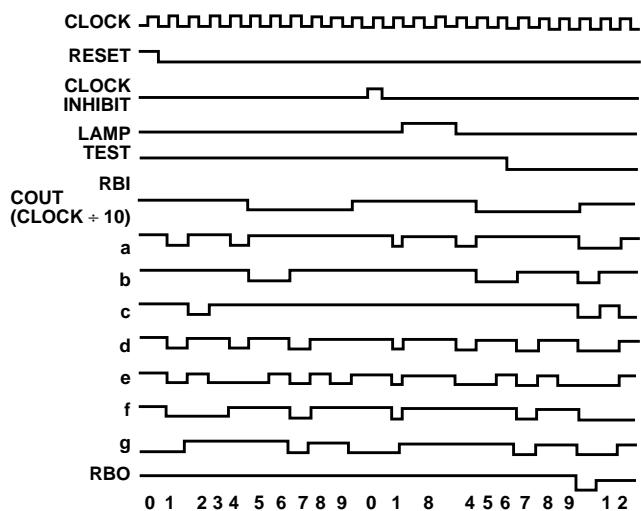


FIGURE 2. CD4033BMS TIMING DIAGRAM

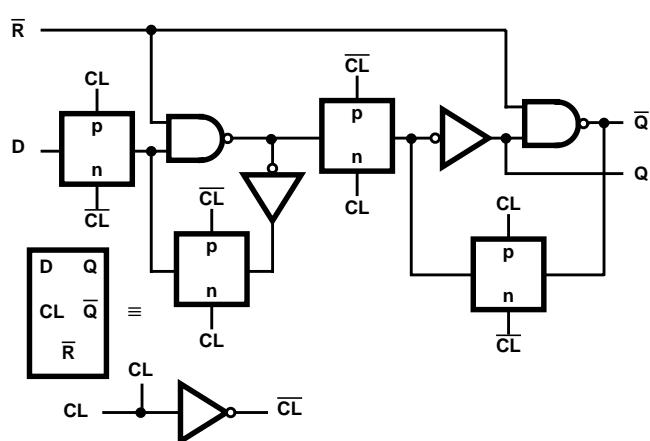


FIGURE 3. DETAIL OF TYPICAL FLIP-FLOP STAGE

Typical Performance Characteristics

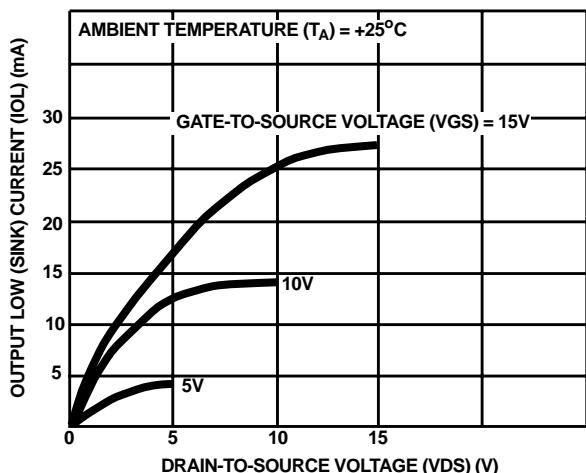


FIGURE 4. TYPICAL N-CHANNEL OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

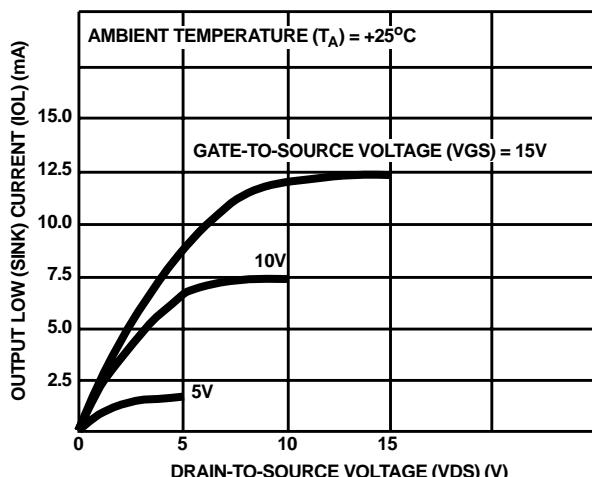


FIGURE 5. MINIMUM N-CHANNEL OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

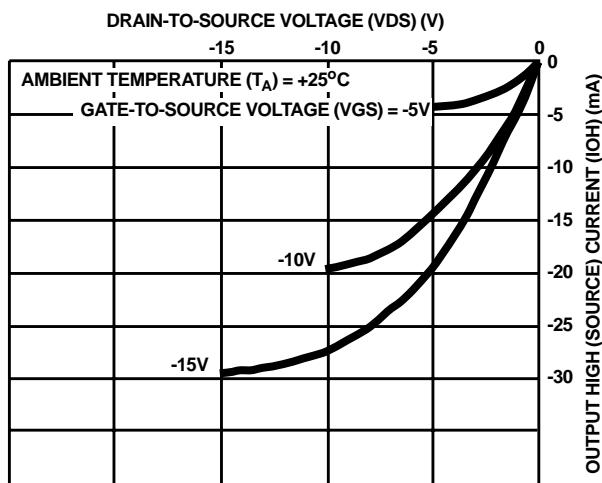


FIGURE 6. TYPICAL P-CHANNEL OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

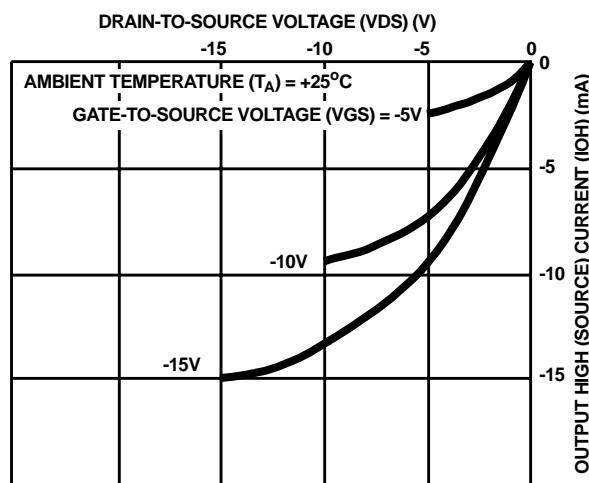


FIGURE 7. MINIMUM P-CHANNEL OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

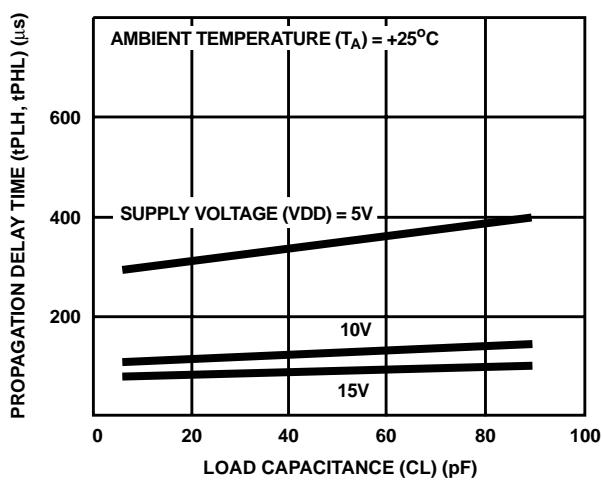


FIGURE 8. TYPICAL PROPAGATION DELAY TIME AS A FUNCTION OF LOAD CAPACITANCE FOR DECODED OUTPUTS

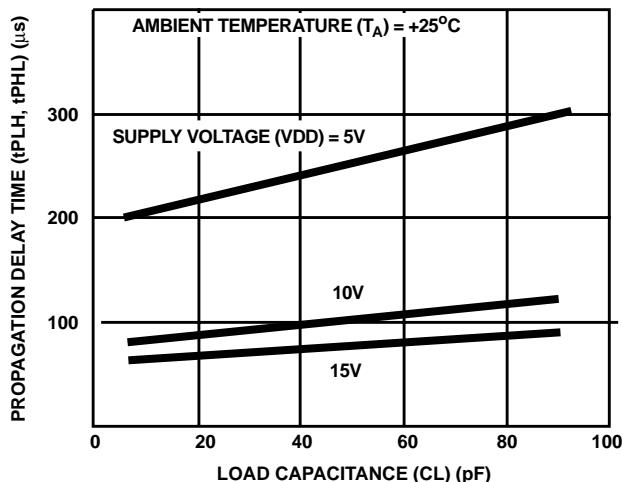


FIGURE 9. TYPICAL PROPAGATION DELAY TIME AS A FUNCTION OF LOAD CAPACITANCE FOR CARRY-OUT OUTPUTS

Typical Performance Characteristics (Continued)

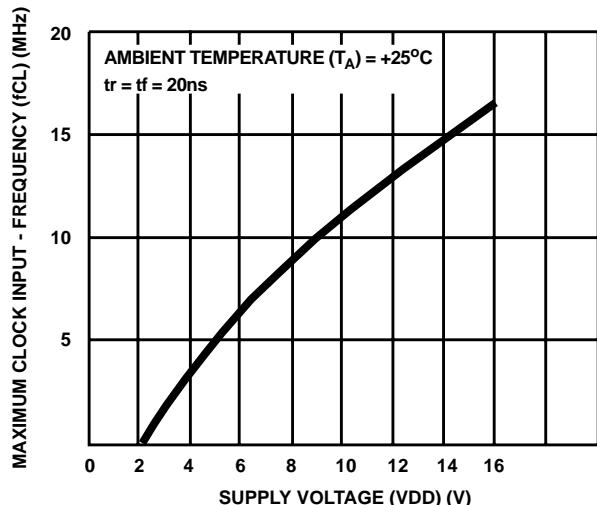


FIGURE 10. TYPICAL MAXIMUM CLOCK INPUT FREQUENCY AS A FUNCTION OF SUPPLY VOLTAGE

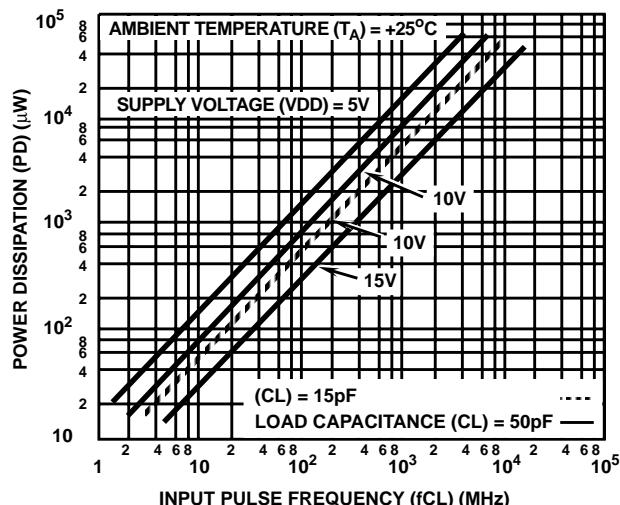


FIGURE 11. TYPICAL POWER DISSIPATION AS A FUNCTION OF CLOCK INPUT FREQUENCY

Light Emitting Diode Displays

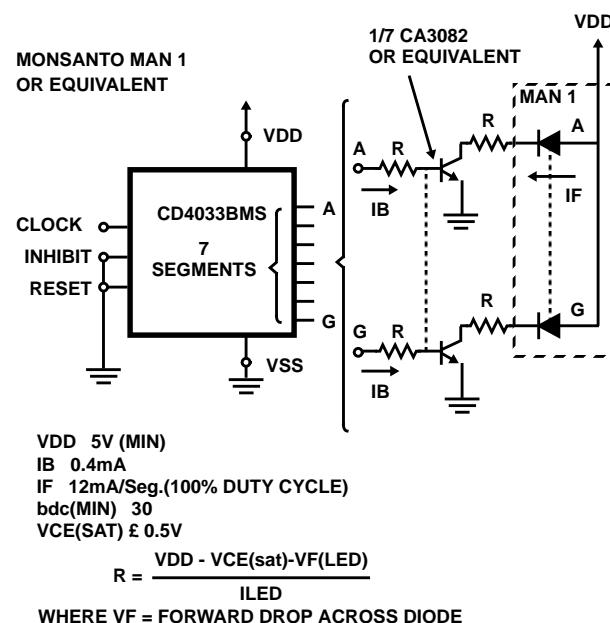
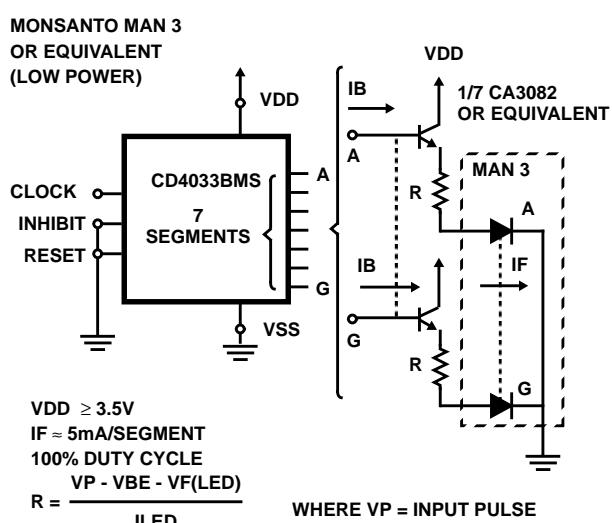
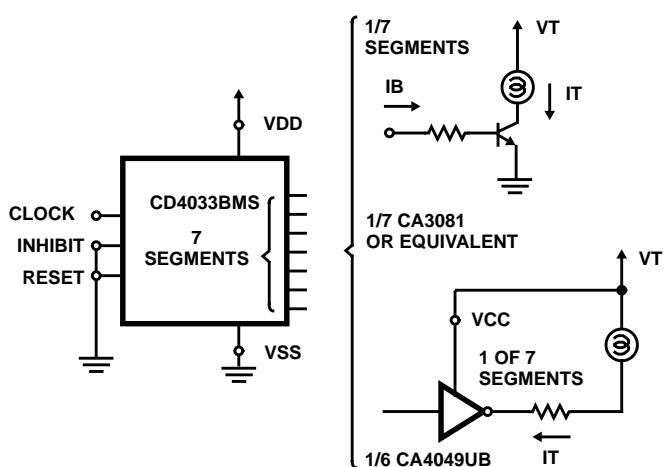


FIGURE 12. INTERFACING THE CD4033BMS WITH COMMERCIALLY AVAILABLE LIGHT EMITTING DIODE DISPLAYS

7-Segment Display Devices



INCANDESCENT READOUTS

Numitron DR2000 Series
TUBE REQUIREMENTS
VT = 3.5 - 5V
IT = 24mA Segment

ASSUMED TRANSISTOR CHARACTERISTICS

CD4049UB at VCC = 10V (min)
Vo "0" ≤ 2V
IT = 8mA (min)
VT ≈ 3.5V to 6V

CD4049UB at VCC = 10V (min)
Vo "0" ≤ 0.6V
IT = 8mA (min)

at VCC = 6V (min)
Vo "0" ≤ 1V
IT = 5mA (min)
VT ≈ 1.5V to 3.5V

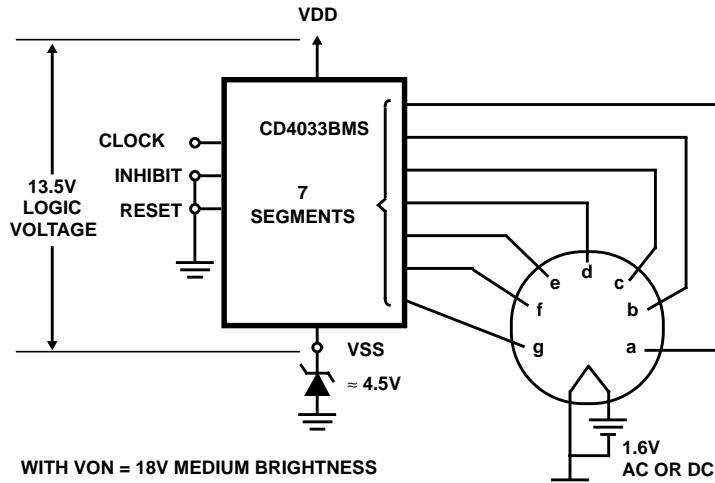
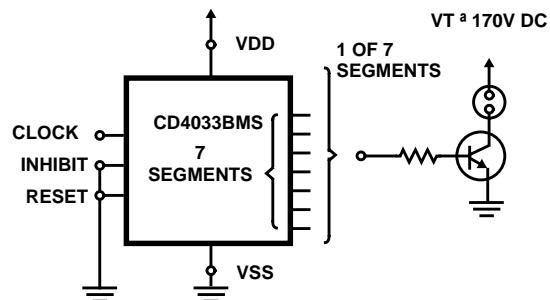
LOW-POWER INCANDESCENT READOUTS

PINLITES INC-Series O and R

ASSUMED TRANSISTOR CHARACTERISTICS

TUBE REQUIREMENTS	VT(V)	mA/Segment	βdc (min) ≥ 30 VCE (sat) ≤ 0.5V
0-03-15	1.5	8	
0-04-30	3	8	
0-06-30	3	8	VCC ≥ 3.5V (min)
R-R3-20	2	4.3	IB ≥ 0.25mA (min)
R-R4-30	3	4.3	IT ≤ 7.5mA (min)

*The interfacing buffers shown, while a necessity with the CD4033A, are not required when using the "B" devices; the "B" outputs (~ 10 times the "A" outputs) can drive most display devices directly especially at voltages above 10V.



NEON READOUT (NIXIE TUBE**)

1. Alco Electronics - MG19
2. Burroughs - B5971, B7971, B8971

WITH VON = 18V MEDIUM BRIGHTNESS
IN LOW AMBIENT LIGHT BACKGROUND
WILL RESULT. THE POINT OF NO
NOTICEABLE GLOW IS VOFF ≈ 4.5V

TUBE REQUIREMENTS

	VT(Vdc)	mA/Segment
Alco MG19	180	0.5
Burroughs B5971	170	3
Burroughs B7971, B8971	170	6

LOW VOLTAGE VACUUM FLORESCENT READOUTS

1. Tung-Sol DIGIVAC S/G ‡ Type DT1704A or DT1705C
2. Nippon Electric (NEC): Type DG12E or LD915

TUBE REQUIREMENTS: 100 to 300 μ A/segment at tube voltages of 12V to 25V depending on required brightness Filament requirement 45mA at 1.6V, ac or dc.

**(Trademark) Burroughs Corp.

TRANSISTOR CHARACTERISTICS

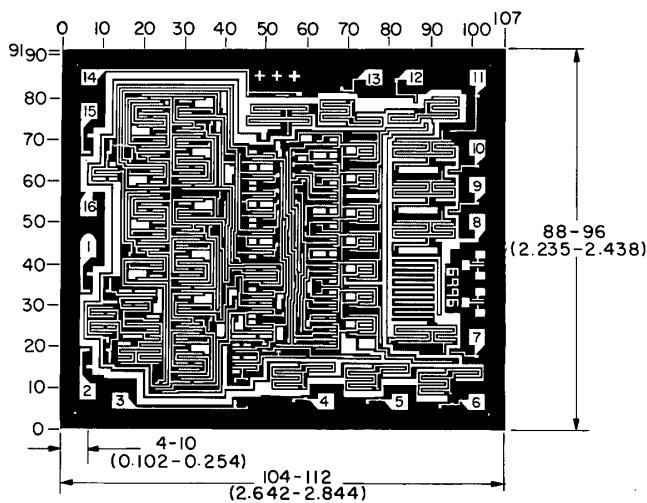
Leakage with transistor cutoff - 0.05mA

V(BR)CER > VT

β_{dc} (min) ≥ 30

‡ (Trademark) Wagner Electric Co.

FIGURE 13. INTERFACING THE CD4033BMS WITH COMMERCIALLY AVAILABLE 7-SEGMENT DISPLAY DEVICES*

Chip Dimensions and Pad Layouts

Dimensions in parentheses are in millimeters
and are derived from the basic inch dimensions
as indicated. Grid graduations are in mils (10^{-3} inch)

METALLIZATION: Thickness: $11\text{k}\text{\AA}$ – $14\text{k}\text{\AA}$, AL.

PASSIVATION: $10.4\text{k}\text{\AA}$ - $15.6\text{k}\text{\AA}$, Silane

BOND PADS: 0.004 inches X 0.004 inches MIN

DIE THICKNESS: 0.0198 inches - 0.0218 inches

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